

AMENDMENTS TO THE SPECIFICATION

IN THE ABSTRACT OF THE DISCLOSURE:

Replace the Abstract of the Disclosure currently of record with the attached new Abstract of the Disclosure.

--A non-volatile passive matrix memory device includes an electrically polarizable dielectric memory material exhibiting hysteresis, first and second sets of addressing electrodes constitute word lines and bit lines of the memory device. The word lines are divided into segments with each segments sharing and being defined by adjoining bit lines. Means are provided for connecting each bit line of a segment with a sensing mean, thus enabling simultaneous connections of all memory cells of a word line segment for readout via the bit lines of the segment. Each sensing means senses the charge flow in a bit line in order to determine a stored logical value.--